# Particam: A fully digital sensor for sub micron resolution

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### Motivation:

Over the past decades the spatial resolution of pixel sensors has only marginally improved. Analogue frontends require larger transistor sizes for optimal performance discouraging miniaturisation and the adoption of smaller process nodes.

 $\rightarrow$ A new approach is needed to achieve a sub micron spatial resolution Solution:

Implement the pixel cell as single bit memory cell and harness





- Pixels respond to laser light but only some flavours detect alphas
- Broken address decoders in

## Particam1 [1]:

- Implemented in the 65nm UMC node



### Working Principle:

Aggressive (**a**+**b**) and Custom (**c**+**d**) array are implemented as imbalanced flip-flop. Charge induces a flip from 1 to 0 at very low threshold charge  $C_T$  compared to the Standard SRAM cell while the opposite flip is strongly suppressed. Transistor leakage current "precharges" the pixel after reset but can also cause the pixel to flip. Increasing DV=VDD-V<sub>high</sub>=V<sub>low</sub>-GND



small pixel matrices

Periodic resets required due to leakage





3

# First Application:

- Coat sensors in boron carbide converter layer for neutron detection at PSI
- First attempt on coating of bare dies unsuccessful
- Coating bonded sensors on carrier in progress









#### Outlook:

- Particam2, produced in the LFoundry 110nm node, was received recently and is being tested
- Particam2 has a 14µm high resistivity epi-layer and a VBD of ~70V
- Extensive survey of possible process nodes for future designs is ongoing
- Identify possible applications within (linear



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